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REVOCATION AND NEW POWER OF ATTORNEY AND
CHANGE OF CORRESPONDENCE ADDRESS

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

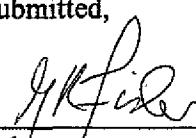
Customer Number: 76681

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

Customer Number: 76681

Respectfully submitted,

Date: 5/13/2008


Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)

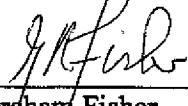
MEMC Electronic Materials, Inc., a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in ***U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.***

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to ***MEMC Electronic Materials, Inc.*** via Assignment(s) recorded with the United States Patent and Trademark Office at the ***Reel/Frame Numbers on the attached Schedule A.***

The undersigned, ***Dr. Graham Fisher, Director of Intellectual Property***, has full authorization to act on behalf of Assignee ***MEMC Electronic Materials, Inc.***

Respectfully submitted,

Date: 5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

APPENDIX A
Owned by MEMC Electronic Materials, Inc.

ATTORNEY REFERENCE	CONF. NO	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
28744-177 (MEMC3114.1)	4497	US2007-0045738-A1 3/1/2007	11/461,956 8/22/2006	MEMC Electronic Materials, Inc.	018400/00456		METHOD FOR THE MANUFACTURE OF A STRAINED SILICON-ON- INSULATOR STRUCTURE
28744-60 (MEMC3115.1)	3973	US2007-0042566-A1 2/22/2007	11/461,653 8/1/2006	MEMC Electronic Materials, Inc.	018486/00447		STRAINED SILICON ON INSULATOR (SSOI) STRUCTURE WITH IMPROVED CRYSTALLINITY IN THE STRAINED SILICON LAYER
28744-155 (MEMC3116)	5718	US2006-0231055-A1 10/19/2006	11/107,444 4/15/2005	MEMC Electronic Materials, Inc.	016278/00974		MODIFIED SUSCEPTOR FOR BARREL REACTOR
28744-346 (MEMC3126)	59475	US2007-0249138-A1 10/25/2007	11/408,503 4/2/2006	MEMC Electronic Materials, Inc.	017974/00835		SILICON STRUCTURES WITH IMPROVED RESISTANCE TO RADIATION EVENTS
28744-347 (MEMC3127.1)	4131	US2007-0119659-A1 8/27/2007	11/611,430 12/29/2006	MEMC Electronic Materials, Inc.	019136/00568		DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY
28744-349 (MEMC3128.1)	5925	US2007-0176238-A1 8/12/2007	11/698,723 11/26/2007	MEMC Electronic Materials, Inc.	019110/00543		SILICON WAFER WITH HIGH THERMAL CONDUCTIVITY
28744-351 (MEMC3131.1)	2048	US2007-0115807-A1 8/12/2007	11/621,920 11/01/2007	MEMC Electronic Materials, Inc.	019177/00655		WIRE SAWING/SLICING SYSTEM AND METHOD WITH INGOT PREHEATING, WEB PREHEATING, SLURRY TEMPERATURE CONTROL, AND/OR SLURRY FLOW RATE CONTROL
MEMC3139	2638	US2007-0117350-A1 5/24/2007	11/616,485 12/27/2006	MEMC Electronic Materials, Inc.	018686/00557		WAFER SUPPORT AND METHOD OF MAKING WAFER SUPPORT
28744-63 (MEMC3151)	2685	US2007-0117350-A1 5/24/2007	11/616,517 12/27/2006	MEMC Electronic Materials, Inc.	018823/00530		STRAINED SILICON ON INSULATOR (SSOI) WITH LAYER TRANSFER FROM OXIDIZED DONOR
28744-147 (MEMC3152)	8867		11/614,129 12/21/2006	MEMC Electronic Materials, Inc.	018935/00398		METHOD OF POLISHING A SEMICONDUCTOR WAFER
28744-354 (MEMC3155)	4137	US2007-0119660-A1 8/12/2007	11/611,433 12/29/2006	MEMC Electronic Materials, Inc.	019136/00619		DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY
28744-170 (MEMC32703.1)	5307	US2007-02224783-A1 9/27/2007	11/753,294 5/24/2007	MEMC Electronic Materials, Inc.	Continuation of 11/058,996 recorded at 9409/0291		PROCESS FOR FORMING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON
28744-356 (MEMC36041.1)	2920	US2007-0238266-A1 10/11/2007	11/753,043 6/14/2007	MEMC Electronic Materials, Inc.	Division of 10/091,985 recorded at 11/0225/0266		NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES
28744-357 (MEMC36053.1)	8402	US-2008-0020148-A1 1/24/2008	11/839,730 6/3/2007	MEMC Electronic Materials, Inc.	Continuation of 10/093,137 which is a continuation of 10/008,084 recorded at 0104/970840		SILICON ON INSULATOR STRUCTURE WITH A SINGLE CRYSTAL CZ SILICON DEVICE LAYER HAVING A REGION WHICH IS FREE OF AGGLOMERATED INTRINSIC POINT DEFECTS
28744-340 (MEMC3094.8)	1290	US-2008-0020684-A1 1/24/2008	10/598,851 5/10/2007	MEMC Electronic Materials, Inc.	U.S. National of PCT based on provisional 60/554,684 recorded at 0153/15/0827 and 015263/0403		WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER